

Description

The SX80P06D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 6V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -60V$ $I_D = -80A$

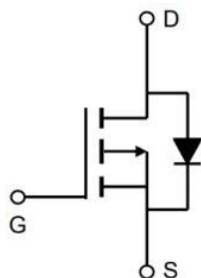
$R_{DS(ON)} < 11m\Omega$ @ $V_{GS} = -10V$

Application

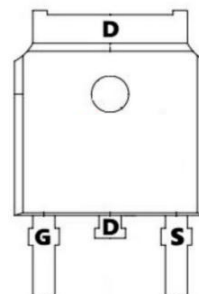
Lithium battery protection

Wireless impact

Mobile phone fast charging



TO-252-3L



Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-80	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $-V_{GS} @ -10V^1$	-50	A
I_{DM}	Pulsed Drain Current ²	-320	A
EAS	Single Pulse Avalanche Energy ³	450	mJ
I_{AS}	Avalanche Current	41	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	110	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	1.1	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	60	$^\circ C/W$

Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60	-68	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.035	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-20A	---	9.0	11	mΩ
		V _{GS} =-4.5V , I _D =-15A	---	12	16	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.8	-2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	4.28	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-60V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-60V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-20A	---	50	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.0	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-30V , V _{GS} =-10V , I _D =-20A	---	56	---	nC
Q _{gs}	Gate-Source Charge		---	11	---	
Q _{gd}	Gate-Drain Charge		---	9	---	
Td(on)	Turn-On Delay Time	V _{DD} =-30V , V _{GS} =-10V , R _G =3Ω , I _D =-20A	---	4.5	---	ns
T _r	Rise Time		---	2.5	---	
Td(off)	Turn-Off Delay Time		---	14.5	---	
T _f	Fall Time		---	3.8	---	
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	3500	---	pF
C _{oss}	Output Capacitance		---	600	---	
Crss	Reverse Transfer Capacitance		---	25	---	
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-80	A
ISM	Pulsed Source Current ^{2,5}		---	---	-240	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is VDD =-48V,VGS =-10V,L=0.1mH,IAS =-41A
- 4、The power dissipation is limited by 150°Cjunction temperature
- 5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

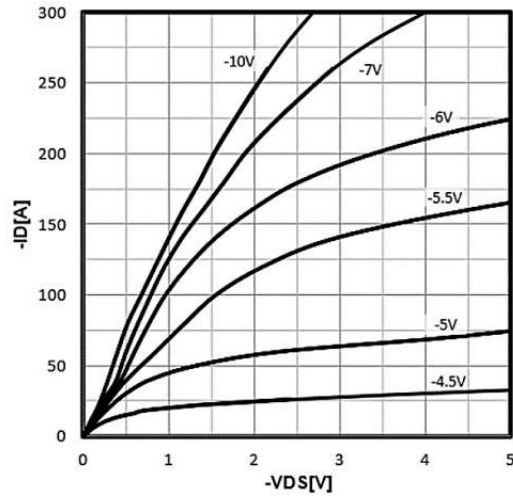


Figure 1. Type. Output Characteristics ($T_j=25\text{ }^{\circ}\text{C}$)

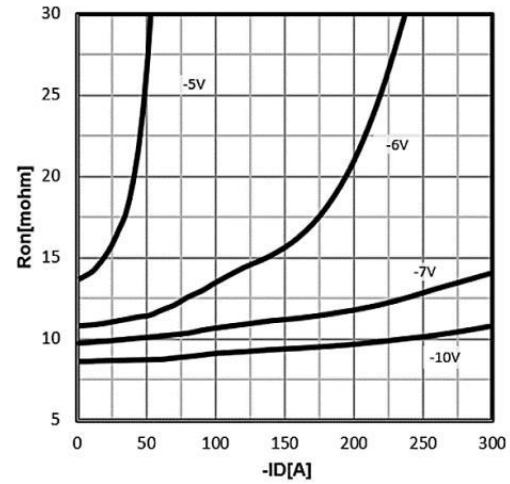


Figure 2. Type. drain-source on resistance

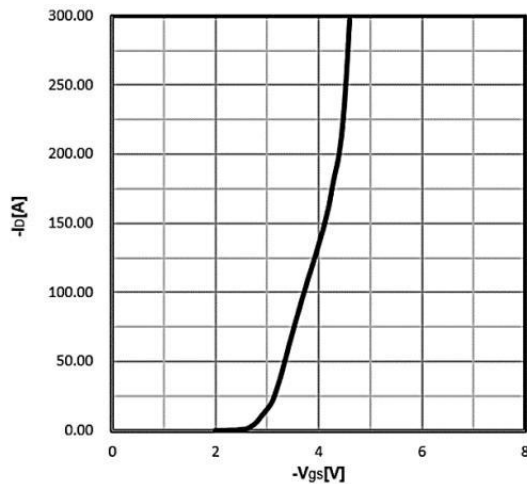


Figure 3. Type. transfer characteristics

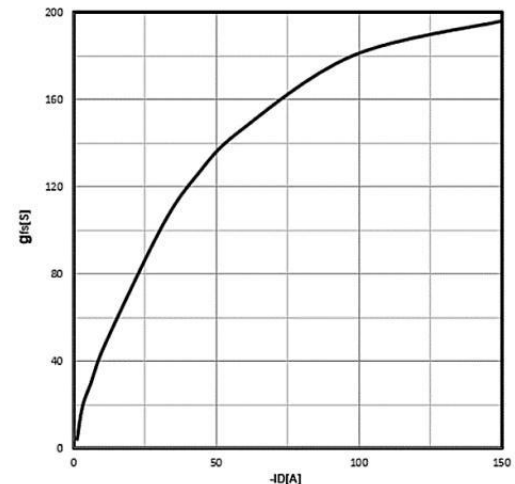


Figure 4. Type. forward transconductance

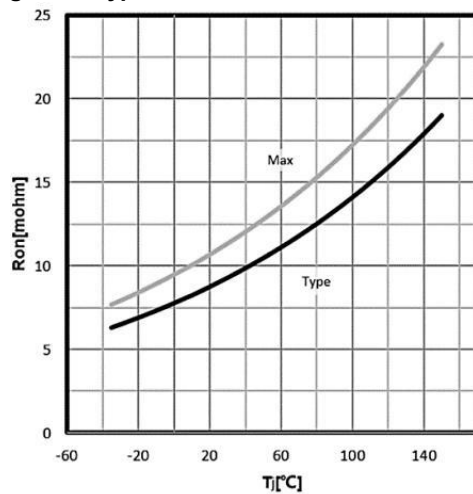


Figure 5. Drain-source on-state resistance $R_{DS(on)} = f(T_j)$; $I_D = 80\text{A}$; $V_{GS} = 10\text{V}$

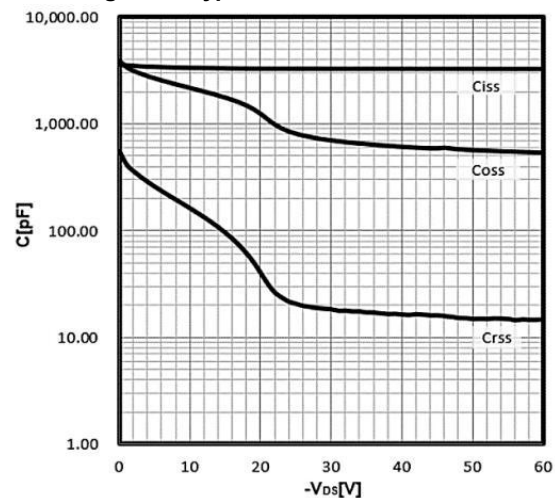


Figure 6. Body-Diode Characteristics $C=f(V_{DS})$; $V_{GS} = 0\text{V}$; $f=1\text{MHz}$

Typical Characteristics

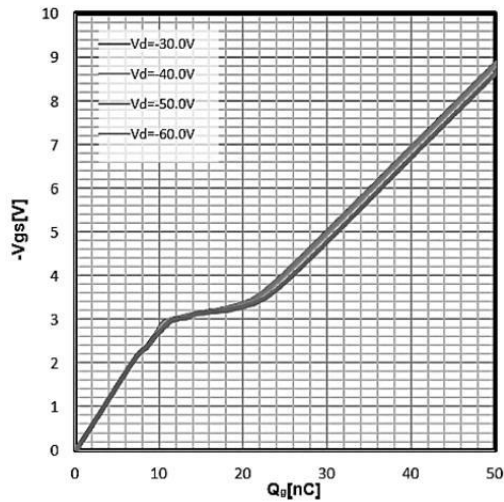


Figure 7. Typ. gate charge
 $V_{GS} = f(Q_{gate})$; $I_D = 20A$

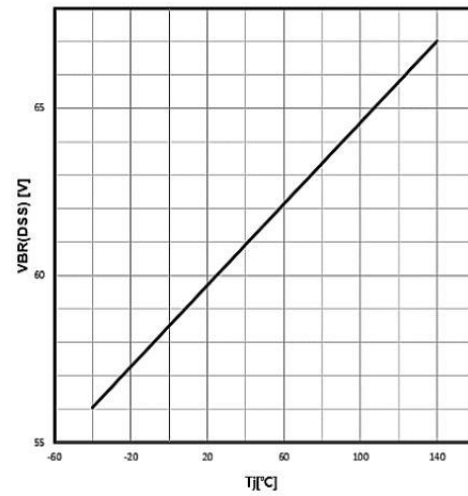


Figure 8. Drain Current Derating
 $V_{BR}(DSS) = f(T_j)$; $I_D = 250\mu A$

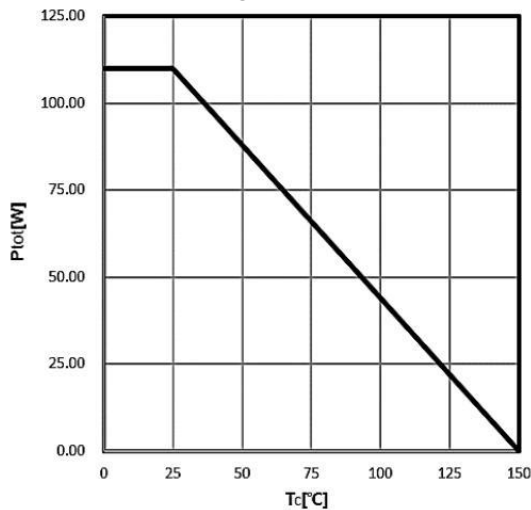


Figure 7. Power Dissipation

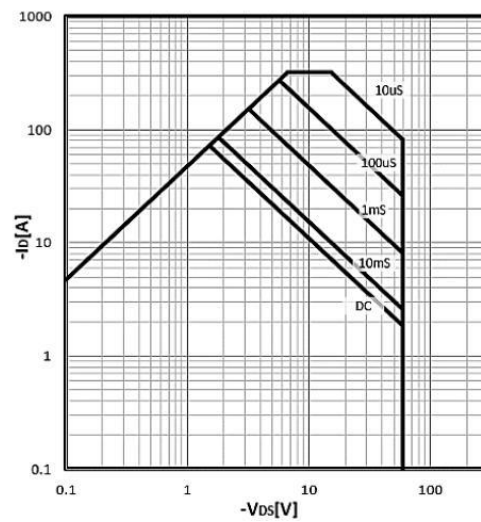


Figure 8. Safe operating area

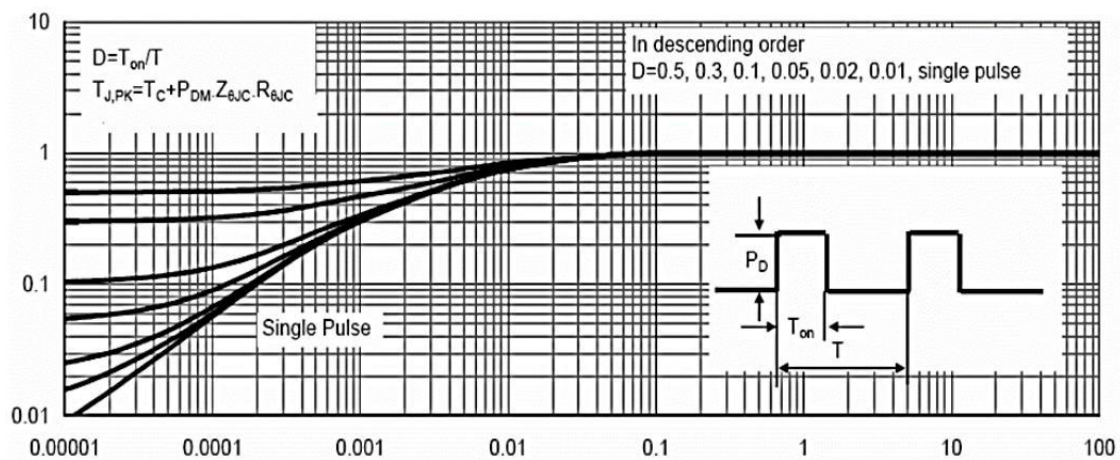
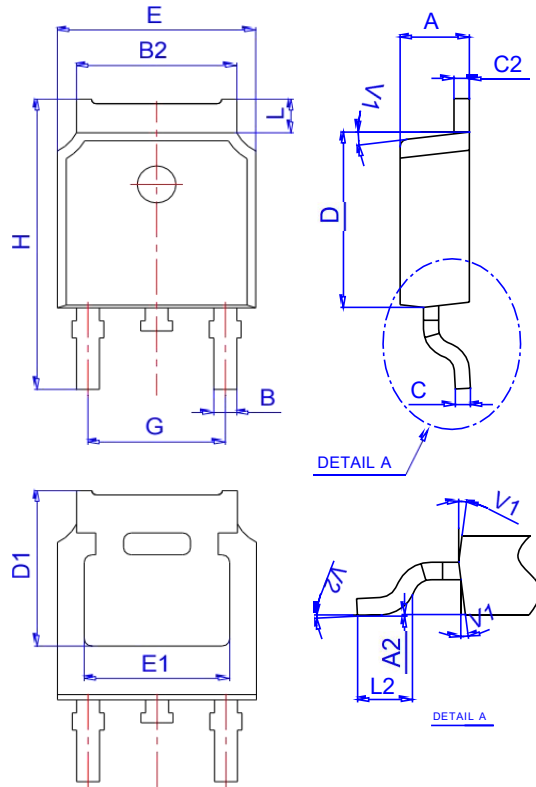


Figure 10. Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500